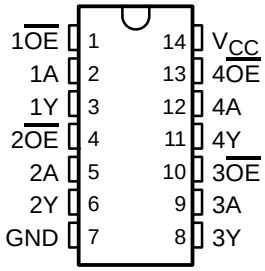
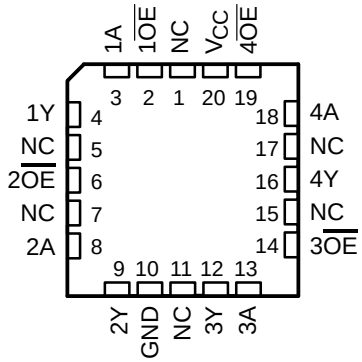
- **Inputs Are TTL-Voltage Compatible**
- **High-Current 3-State Outputs Drive Bus Lines or Buffer Memory Address Registers**
- **Package Options Include Plastic Small-Outline (D) and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) 300-mil DIPs**

SN54HCT125 . . . J OR W PACKAGE
SN74HCT125 . . . D OR N PACKAGE
(TOP VIEW)



SN54HCT125 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

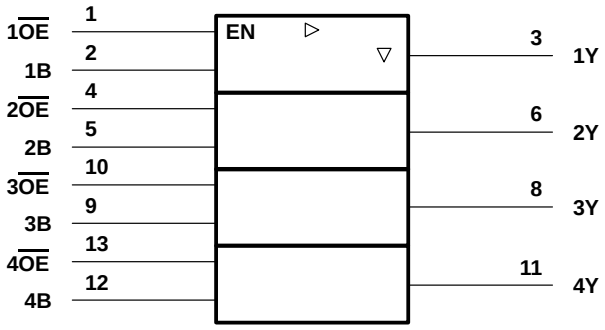
These bus buffer gates feature independent line drivers with 3-state outputs. Each output is disasbled when the associated output-enable ($\overline{OE}$) input is high.

The SN54HCT125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74HCT125 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

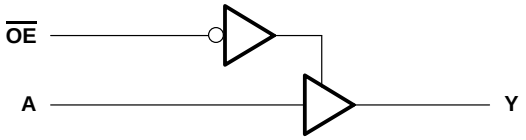
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, J, N, and W packages.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) (see Note 1) . . . . . ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) (see Note 1) . . . . . ±20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) . . . . . ±35 mA
Continuous current through V_{CC} or GND . . . . . ±70 mA
Package thermal impedance, θ_{JA} (see Note 2): D package . . . . . 127°C/W
N package . . . . . 78°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

			SN54HCT125			SN74HCT125			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage		4.5	5	5.5	4.5	5	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 4.5 V to 5.5 V	2			2			V
V_{IL}	Low-level input voltage	V_{CC} = 4.5 V to 5.5 V	0		0.8	0		0.8	V
V_I	Input voltage		0		V_{CC}	0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	0		V_{CC}	V
t_t	Input transition (rise and fall) time		0		500	0		500	ns
T_A	Operating free-air temperature		–55		125	–40		85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	T_A = 25°C			SN54HCT125		SN74HCT125		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	V_I = V_{IH} or V_{IL}	I_{OH} = –20 µA	4.5 V	4.4	4.499		4.4		4.4		V
		I_{OH} = –6 mA		3.98	4.3		3.7		3.84		
V_{OL}	V_I = V_{IH} or V_{IL}	I_{OL} = 20 µA	4.5 V		0.001	0.1		0.1		0.1	V
		I_{OL} = 6 mA			0.17	0.26		0.4		0.33	
I_I	V_I = V_{CC} or 0		5.5 V		±0.1	±100		±1000		±1000	nA
I_{OZ}	V_O = V_{CC} or 0,	V_I = V_{IH} or V_{IL}	5.5 V		±0.01	±0.5		±10		±5	µA
I_{CC}	V_I = V_{CC} or 0,	I_O = 0	5.5 V			8		160		80	µA
ΔI_{CC}†	One input at 0.5 V or 2.4 V, Other inputs at 0 or V_{CC}		5.5 V		1.4	2.4		3		2.9	mA
C_i			4.5 V to 5.5 V		3	10		10*		10	pF

* On products compliant to MIL-PRF-38535, this parameter is not production tested.
† This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			SN54HCT125		SN74HCT125		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	4.5 V		15	26		39		33	ns
			5.5 V		12	23		35		30	
t_{en}	$\overline{OE}$	Y	4.5 V		18	28		42		35	ns
			5.5 V		15	25		38		31	
t_{dis}	$\overline{OE}$	Y	4.5 V		15	26		39		33	ns
			5.5 V		13	23		35		30	
t_t		Any	4.5 V		8	15		22		19	ns
			5.5 V		7	14		21		17	

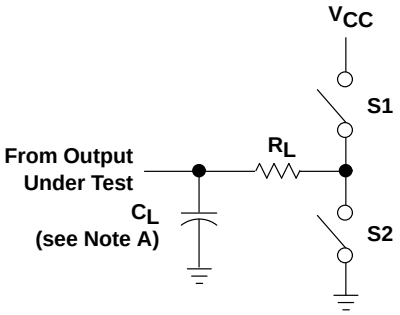
switching characteristics over recommended operating free-air temperature range, C_L = 150 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			SN54HCT125		SN74HCT125		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	4.5 V		19	36		58		46	ns
			5.5 V		16	32		48		42	
t_{en}	$\overline{OE}$	Y	4.5 V		25	40		60		50	ns
			5.5 V		21	35		53		43	
t_t		Any	4.5 V		17	42		63		53	ns
			5.5 V		14	38		57		48	

operating characteristics, T_A = 25°C

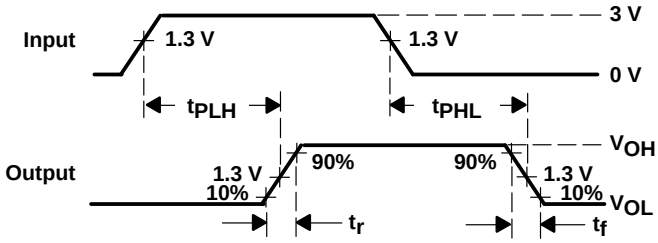
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load	35	pF

PARAMETER MEASUREMENT INFORMATION

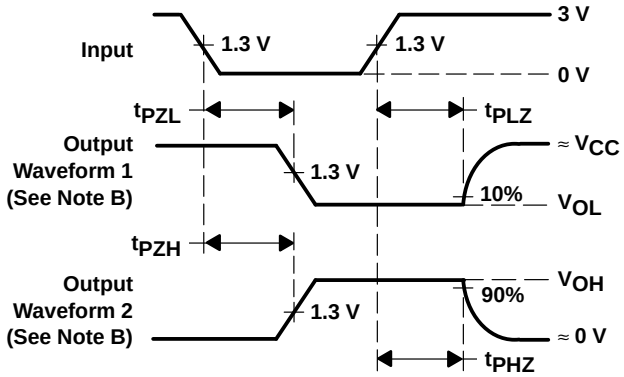


LOAD CIRCUIT

PARAMETER		R_L	C_L	S1	S2
t_{en}	t_{PZH}	1 kΩ	50 pF or 150 pF	Open	Closed
	t_{PZL}			Closed	Open
t_{dis}	t_{PHZ}	1 kΩ	50 pF	Open	Closed
	t_{PLZ}			Closed	Open
t_{pd} or t_t		––	50 pF or 150 pF	Open	Open



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES FOR 3-STATE OUTPUTS

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r = 6 ns, t_f = 6 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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